

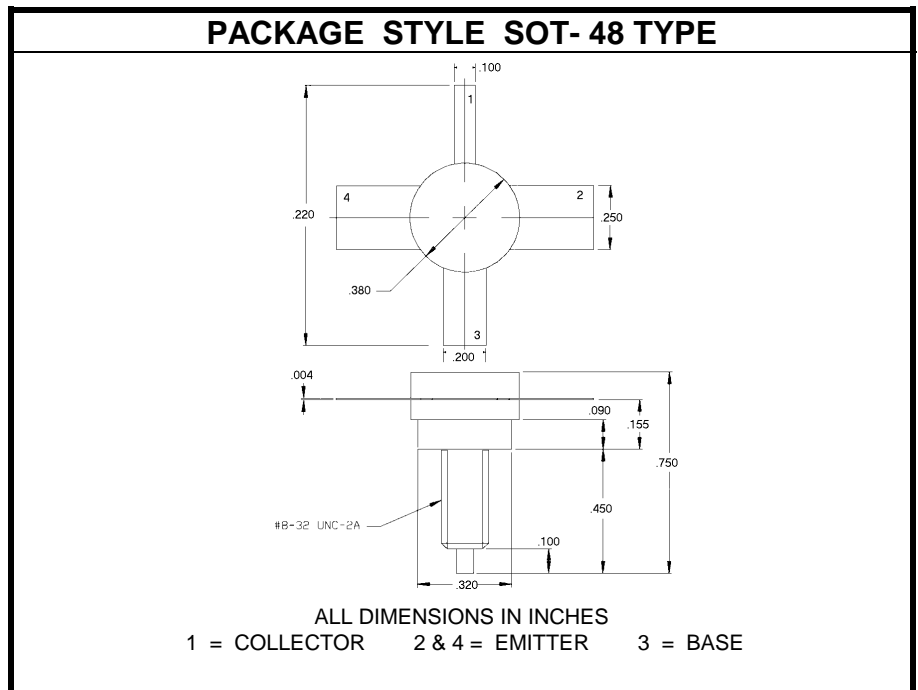
NPN SILICON POWER TRANSISTOR

DESCRIPTION:

The **ASI BLY91A** is Designed for 28 V Class A, B and C Transmitter Applications.

MAXIMUM RATINGS

| | |
|---------------|---|
| I_C | 750 mA 2.25 A (PEAK) $f = \geq 1.0$ MHz |
| V_{CE} | 36 V |
| V_{CB} | 65 V |
| P_{DISS} | 17.5 W @ $T_{mb} = 25^\circ\text{C}$ |
| T_J | -30°C to $+200^\circ\text{C}$ |
| T_{STG} | -30°C to $+200^\circ\text{C}$ |
| θ_{JC} | 9.4 $^\circ\text{C}/\text{W}$ |


CHARACTERISTICS $T_C = 25^\circ\text{C}$

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|------------|--|---------|---------|---------|-------|
| BV_{CEO} | $I_C = 10$ mA | 36 | | | V |
| BV_{CBO} | $I_C = 1.0$ mA | 65 | | | V |
| BV_{EBO} | $I_E = 1.0$ mA | 4.0 | | | V |
| I_{CEO} | $V_{CE} = 28$ V | | | 5.0 | mA |
| h_{FE} | $V_{CE} = 5.0$ V $I_C = 500$ mA | 5.0 | | | --- |
| C_{ob} | $V_{CB} = 30$ V $f = 1.0$ MHz | | 10 | 15 | pF |
| f_t | $V_{CE} = 20$ V $I_C = 400$ mA $f = 500$ MHz | | 500 | | MHz |
| G_p | $V_{CC} = 28$ V $I_C = \leq 0.4$ A $f = 175$ MHz | 12 | | | dB |
| P_L | | 8.0 | | | W |
| η | | 65 | | | % |